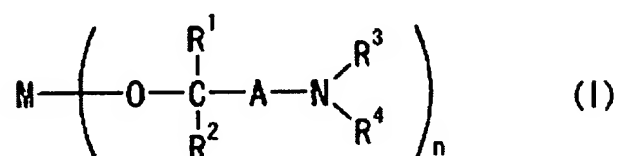


AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): An alkoxide compound represented by general formula (I):



wherein one of R<sup>1</sup> and R<sup>2</sup> represents an alkyl group having 1 to 4 carbon atoms, and the other represents a hydrogen atom or an alkyl group having 1 to 4 carbon atoms; R<sup>3</sup> and R<sup>4</sup> each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.

2. (original): The alkoxide compound according to claim 1, wherein A in general formula (I) is a methylene group.
3. (currently amended): The alkoxide compound according to claim 1 ~~or~~ 2, wherein M in general formula (I) is a silicon atom.
4. (currently amended): The alkoxide metal compound according to claim 1 ~~or~~ 2, wherein M in general formula (I) is a hafnium atom.

5. (currently amended): A material for thin film formation comprising the alkoxide compound according to ~~any one of claims 1 to 4~~ claim 1.
6. (original): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 5, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.
7. (new): ): The alkoxide compound according to claim 2, wherein M in general formula (I) is a silicon atom.
8. (new): The alkoxide metal compound according to claim 4, wherein M in general formula (I) is a hafnium atom.
9. (new): A material for thin film formation comprising the alkoxide compound according to claim 2.
10. (new): A material for thin film formation comprising the alkoxide compound according to claim 3.
11. (new): A material for thin film formation comprising the alkoxide compound according to claim 4.
12. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 9, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.
13. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 10, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.
14. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 11, introducing the resulting vapor containing the

alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.